

Year	1950	1951	1952	1953	1954	1955	1956	1957	1958	1959	1960	1961	1962	1963	1964	1965	1966	1967	1968	1969	1970	1971	1972	1973	1974	1975	1976	1977	1978	1979	1980	1981	1982	1983	1984	1985	1986	1987	1988	1989	1990	1991	1992	1993	1994	1995	1996	1997	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034	2035	2036	2037	2038	2039	2040	2041	2042	2043	2044	2045	2046	2047	2048	2049	2050	2051	2052	2053	2054	2055	2056	2057	2058	2059	2060	2061	2062	2063	2064	2065	2066	2067	2068	2069	2070	2071	2072	2073	2074	2075	2076	2077	2078	2079	2080	2081	2082	2083	2084	2085	2086	2087	2088	2089	2090	2091	2092	2093	2094	2095	2096	2097	2098	2099	2100																			
Population	1,000,000	1,050,000	1,100,000	1,150,000	1,200,000	1,250,000	1,300,000	1,350,000	1,400,000	1,450,000	1,500,000	1,550,000	1,600,000	1,650,000	1,700,000	1,750,000	1,800,000	1,850,000	1,900,000	1,950,000	2,000,000	2,050,000	2,100,000	2,150,000	2,200,000	2,250,000	2,300,000	2,350,000	2,400,000	2,450,000	2,500,000	2,550,000	2,600,000	2,650,000	2,700,000	2,750,000	2,800,000	2,850,000	2,900,000	2,950,000	3,000,000	3,050,000	3,100,000	3,150,000	3,200,000	3,250,000	3,300,000	3,350,000	3,400,000	3,450,000	3,500,000	3,550,000	3,600,000	3,650,000	3,700,000	3,750,000	3,800,000	3,850,000	3,900,000	3,950,000	4,000,000	4,050,000	4,100,000	4,150,000	4,200,000	4,250,000	4,300,000	4,350,000	4,400,000	4,450,000	4,500,000	4,550,000	4,600,000	4,650,000	4,700,000	4,750,000	4,800,000	4,850,000	4,900,000	4,950,000	5,000,000	5,050,000	5,100,000	5,150,000	5,200,000	5,250,000	5,300,000	5,350,000	5,400,000	5,450,000	5,500,000	5,550,000	5,600,000	5,650,000	5,700,000	5,750,000	5,800,000	5,850,000	5,900,000	5,950,000	6,000,000	6,050,000	6,100,000	6,150,000	6,200,000	6,250,000	6,300,000	6,350,000	6,400,000	6,450,000	6,500,000	6,550,000	6,600,000	6,650,000	6,700,000	6,750,000	6,800,000	6,850,000	6,900,000	6,950,000	7,000,000	7,050,000	7,100,000	7,150,000	7,200,000	7,250,000	7,300,000	7,350,000	7,400,000	7,450,000	7,500,000	7,550,000	7,600,000	7,650,000	7,700,000	7,750,000	7,800,000	7,850,000	7,900,000	7,950,000	8,000,000	8,050,000	8,100,000	8,150,000	8,200,000	8,250,000	8,300,000	8,350,000	8,400,000	8,450,000	8,500,000	8,550,000	8,600,000	8,650,000	8,700,000	8,750,000	8,800,000	8,850,000	8,900,000	8,950,000	9,000,000	9,050,000	9,100,000	9,150,000	9,200,000	9,250,000	9,300,000	9,350,000	9,400,000	9,450,000

Prompt and favorable action is earnestly solicited.

Respectfully submitted,

[Handwritten signature]

Atty. Docket No. **981206A**
1725 K Street, N.W., Suite 1000
Washington, DC 20006
Tel: (202) 659-2930
Fax: (202) 887-0357

Attachment: Version with markings to show changes made

VERSION WITH MARKINGS TO SHOW CHANGES MADE
DIVISIONAL OF (09/161,828)

IN THE SPECIFICATION:

The specification has been amended as follows:

Paragraph beginning at page 6, line 11 has been amended as follows:

As shown in Fig. 1, a first aspect of the present invention is a device of a semiconductor device, which comprises: a semiconductor substrate of a ~~firstconduction~~ first conduction type; a drain layer of the first conduction type and formed on a surface layer of the semiconductor substrate; a gate insulating film formed in a partial region on the drain layer; a gate electrode formed on the gate insulating film; an insulating film formed on the gate electrode; a side wall insulator formed on side walls of the gate insulating film, the gate electrode, and the insulating film; a recess formed on the drain layer and in a region other than a region where the gate electrode and the side wall insulator are formed; a channel layer of an opposite conduction type and formed in a range from the region where the recess is formed to a vicinity of the region where the gate electrode is formed; a source region layer of the one conduction type and formed on the channel layer in a region outside the recess; and a wiring layer formed to cover the channel layer which is exposed through the recess, the side wall insulator, and the insulating film.

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IN THE CLAIMS:

Claims 12-14 and 16 have been amended as follows:

12. (Amended) A method of fabricating a semiconductor device, comprising the steps of:

forming a drain layer of a first conduction type on a surface of a semiconductor substrate of the first conduction type;

forming a first insulating film on said drain layer;

forming a first conductive layer on said first insulating film;

forming a second insulating film on said first conductive layer;

patterning said second insulating film, said first conductive layer, and said first insulating film, to form a gate insulating film from said first insulating film, and a gate electrode from said first conductive layer;

implanting an impurity of a second conduction type opposite to the first conduction type into a surface of said drain layer with using said gate electrode as a mask, thereby forming a channel region of the second conduction type;

implanting an impurity of the first conduction type into said channel region with using said gate electrode as a mask, thereby forming a an impurity region of the first conduction type;

forming a third insulating film so as to cover a surface of the

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impurity region, side walls of said gate insulating film, said gate electrode, and said second insulating film, and an upper face of said second insulating film;

etching back said third insulating film to form a side wall insulator consisting of said third insulating film, by remaining said third insulating film selectively on side walls of said gate insulating film, said gate electrode, and said second insulating film;

etching the impurity region to form a recess so as to penetrate the impurity region, thereby forming a source region consisting of the impurity region; and

forming a second conductive layer on an entire surface, and patterning said second conductive layer, thereby forming a wiring layer.

13. (Amended) The method of fabricating a semiconductor device, according to the claim 12, wherein further comprising a step of:

introducing an impurity of the second conduction type into the bottom of the recess to form a body contact region of the second conduction after etching the impurity region prior to forming a second conductive layer.

14. (Amended) The method of fabricating a semiconductor device, according to the claim 12, wherein the etching step comprises the steps of:

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forming a mask pattern having an opening located in a center of the ~~source~~ impurity region and cover an entire surface except for the opening before etching the impurity region;

etching the impurity region by using the mask pattern to form a recess ~~shallower than the exposed surface of the impurity region so as to penetrate~~ deeper than the impurity region, thereby forming a source region of the impurity region remained; and

introducing an impurity of the second conduction type into the bottom of the recess to form a body contact region of the second conduction type.

16. (Amended) A method of fabricating a semiconductor device, comprising the steps of:

forming a drain layer of a first conduction type on a surface of a semiconductor substrate of the first conduction type;

introducing an impurity of a second conduction type opposite to the first conduction type into an entire surface of said drain layer, thereby forming a channel layer;

forming a trench so as to penetrate said channel layer and reach said drain layer using a first mask;

forming a first insulating film on an inner wall of said trench and a

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surface of said channel layer;

forming a conductive layer on said first insulating film;

forming a second insulating film on said conductive layer;

patterning said second insulating film, said conductive layer, and said first insulating film with using a same second mask, to form a gate insulating film of said first insulating film, and a gate electrode of said conductive layer;

implanting an impurity of the first conduction type into a surface of said channel layer with using said gate electrode as a mask, thereby forming a impurity region of the first conduction type;

forming a third insulating film on an entire surface;

etching back said third insulating film to form a side wall insulator which covers side walls of said gate insulating film, said gate electrode, and said first insulating film;

forming a third mask having an opening located in a center of the ~~source~~ impurity region and cover an entire surface except for the opening, before etching the impurity region;

etching the impurity region by using the third mask to form a recess ~~shallower than the exposed surface of the impurity region so as~~ to penetrate the impurity region and reach to the channel region, thereby forming a source region ~~consisting~~ of the impurity region; and

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implanting an impurity of the second conduction type into a
bottom of said recess, with remaining said third mask, thereby forming a body contact region;
and

removing said third mask; and

forming a second conductive layer which covers said source
region, said body contact region, said side wall insulator, and said second insulating film, and
patterning said second conductive layer by using a fourth mask, thereby forming a wiring layer.